

PERFORMANCE SPECIFICATION SHEET

SEMICONDUCTOR DEVICE, DIODE, SILICON, DUAL, SCHOTTKY,
COMMON CATHODE, TYPE 1N7070CCT3, JAN, JANTX, JANTXV, AND JANS

This specification is approved for use by all Departments and Agencies of the Department of Defense.

The requirements for acquiring the product described herein shall consist of this specification sheet and MIL-PRF-19500.

1. SCOPE

1.1 Scope. This specification covers the performance requirements for a silicon, Schottky dual power rectifier diode for use in high frequency switching power supplies and resonant power converters. Four levels of product assurance are provided for each device type as specified in MIL-PRF-19500.

1.2 Physical dimensions. See figure 1, T3 (TO-257) package.

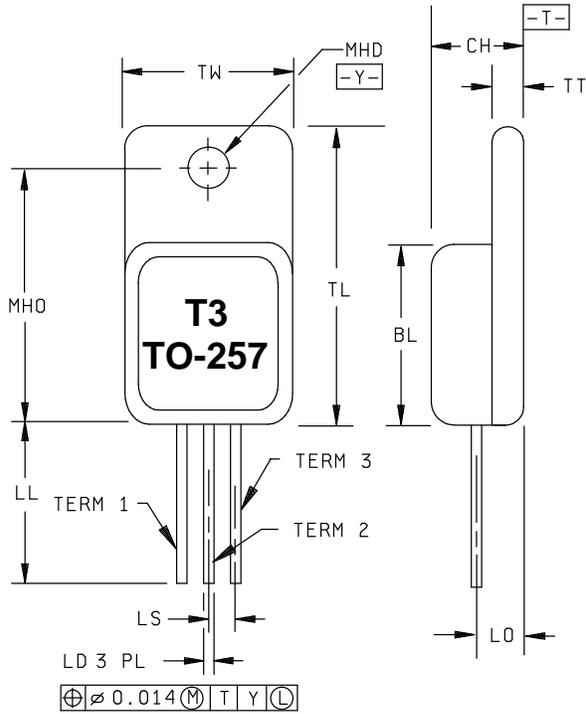
1.3 Maximum ratings. Unless otherwise specified, $T_C = +25^\circ\text{C}$.

Column 1	Column 2	Column 3	Column 4	Column 5		Column 6
Types	V_{RWM}	I_O (1)(2) $T_C = +100^\circ\text{C}$	I_{FSM} (2) $t_p = 8.3 \text{ ms}$ $T_C = +25^\circ\text{C}$	$R_{\theta JC}$ (2)	$R_{\theta JC}$ (3)	T_{STG} and T_J
	V dc	A dc	A (pk)	$^\circ\text{C/W}$	$^\circ\text{C/W}$	$^\circ\text{C}$
1N7070CCT3	100	16	250	1.0	2.0	-65 to +150

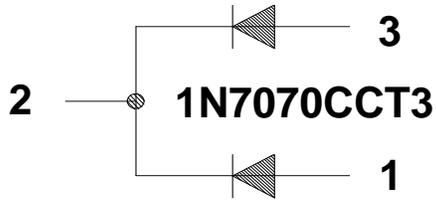
- (1) See temperature-current derating curves on figure 2.
(2) Entire package.
(3) Each leg.

1.4 Primary electrical characteristics. $R_{\theta JC} = 1.0^\circ\text{C/W}$ maximum entire package for 1N7070CCT3; $R_{\theta JC} = 2.0^\circ\text{C/W}$ maximum each leg (figure 3); $R_{\theta JA} = 80^\circ\text{C/W}$ maximum.

Comments, suggestions, or questions on this document should be addressed to Defense Supply Center, Columbus, ATTN: DSCC-VAC, P.O. Box 3990, Columbus, OH 43218-3990, or emailed to Semiconductor@dsc.dla.mil. Since contact information can change, you may want to verify the currency of this address information using the ASSIST Online database at <https://assist.daps.dla.mil>.



Ltr	Dimensions			
	Inches		Millimeters	
	Min	Max	Min	Max
BL	.410	.430	10.41	10.92
CH	.190	.200	4.83	5.08
LD	.025	.035	0.64	0.88
LL	.500	.750	12.70	19.05
LO	.120 BSC		3.05 BSC	
LS	.100 BSC		2.54 BSC	
MHD	.140	.150	3.56	3.81
MHO	.527	.537	13.39	13.64
TL	.645	.665	16.38	16.89
TT	.035	.045	0.89	1.14
TW	.410	.420	10.41	10.67



NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. In accordance with ASME Y14.5M, diameters are equivalent to \varnothing x symbology.

FIGURE 1. Dimensions and configuration TO-257 (T3).

2. APPLICABLE DOCUMENTS

2.1 General. The documents listed in this section are specified in sections 3, 4, or 5 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements of documents cited in sections 3, 4, or 5 of this specification, whether or not they are listed.

2.2 Government documents.

2.2.1 Specifications, standards, and handbooks. The following specifications, standards, and handbooks form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATIONS

MIL-PRF-19500 - Semiconductor Devices, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-750 - Test Methods for Semiconductor Devices.

(Copies of these documents are available online at <https://assist.daps.dla.mil/quicksearch> or <https://assist.daps.dla.mil> or from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.3 Order of precedence. Unless otherwise noted herein or in the contract, in the event of a conflict between the text of this document and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 General. The individual item requirements shall be as specified in MIL-PRF-19500 and as modified herein.

3.2 Qualification. Devices furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturer's list (QML) before contract award (see 4.2 and 6.3).

3.3 Abbreviations, symbols, and definitions. Abbreviations, symbols, and definitions used herein shall be as specified in MIL-PRF-19500.

3.4 Interface and physical dimensions. The interface and physical dimensions shall be as specified in MIL-PRF-19500, and on figure 1 herein.

3.4.1 Polarity. Polarity and terminal configuration shall be in accordance with figure 1 herein.

3.4.2 Lead material, finish, and formation. Lead material shall be Kovar or Alloy 52; a copper core or plated core is permitted. Lead finish shall be solderable in accordance with MIL-PRF-19500, MIL-STD-750, and herein. Where a choice of lead formation, material, or finish is desired, it shall be specified in the acquisition document (see 6.2). When lead formation is performed, as a minimum, the vendor shall perform 100 percent hermetic seal in accordance with screen 14 of table E-IV of MIL-PRF-19500 and 100 percent dc testing in accordance with table I, subgroup 2 herein.

3.5 Electrical performance characteristics. Unless otherwise specified herein, the electrical performance characteristics are as specified in 1.3, 1.4, and table I herein.

3.6 Electrical test requirements. The electrical test requirements shall be as specified in tables I and II herein.

3.7 Marking. Marking shall be in accordance with MIL-PRF-19500 and herein.

3.8 Workmanship. Semiconductor devices shall be processed in such a manner as to be uniform in quality and shall be free from other defects that will affect life, serviceability, or appearance.

4. VERIFICATION

4.1 Classification of inspections. The inspection requirements specified herein are classified as follows:

- a. Qualification inspection (see 4.2).
- b. Screening (see 4.3).
- c. Conformance inspection (see 4.4 and tables I and II herein).

4.2 Qualification inspection. Qualification inspection shall be in accordance with MIL-PRF-19500 and as specified herein.

4.2.1 Group E qualification. Group E inspection shall be performed for qualification or re-qualification only. In case qualification was awarded to a prior revision of the specification sheet that did not request the performance of table III tests, the tests specified in table III herein that were not performed in the prior revision shall be performed on the first inspection lot of this revision to maintain qualification.

4.3 Screening (JANS, JANTXV, and JANTX levels). Screening shall be in accordance with table E-IV of MIL-PRF-19500 and as specified herein. The following measurements shall be made in accordance with table I herein. Devices that exceed the limits of table I herein shall not be acceptable.

Screen (see table E-IV of MIL-PRF-19500)	Measurement	
	JANS level	JANTX and JANTXV levels
3b	Method 4066 of MIL-STD-750, condition A, one pulse, $t_p = 8.3$ ms, $I_O = 0$, $V_{RWM} = 0$, $I_{FSM} =$ see 1.3 herein.	Method 4066 of MIL-STD-750, condition A, one pulse, $t_p = 8.3$ ms, $I_O = 0$, $V_{RWM} = 0$, $I_{FSM} =$ see 1.3 herein.
3c	Thermal impedance (see 4.3.2).	Thermal impedance (see 4.3.2).
3d	Avalanche energy test (see 4.3.3).	Avalanche energy test (see 4.3.3).
9, 10	Not applicable.	Not applicable.
11	V_{F1} and I_{R1} .	V_{F1} and I_{R1} .
12	$t = 240$ hours minimum. See 4.3.1.	$t = 48$ hours minimum. See 4.3.1.
13	Subgroup 2 and 3, of table I herein, V_{F1} and I_{R1} ; $\Delta V_{F2} = \pm 50$ mV (pk); $\Delta I_{R1} = \pm 100$ percent from the initial value or $\pm 2\mu A$, whichever is greater.	Subgroup 2, of table I herein; V_{F1} and I_{R1} ; $\Delta V_{F2} = \pm 50$ mV (pk); $\Delta I_{R1} = \pm 100$ percent from the initial value or $\pm 2\mu A$, whichever is greater.

4.3.1 Power burn-in conditions. Burn-in conditions are as follows: Method 1038 of MIL-STD-750, test condition A. $T_J = +125^\circ C$; $V_R = 80$ V dc.

4.3.2 Thermal impedance. The thermal impedance measurements shall be performed in accordance with method 3101 or 4081 of MIL-STD-750 using the guidelines in that method for determining I_M , I_H , t_H , and t_{MD} . Measurement delay time (t_{MD}) = 70 μs max, and figure 3. See table III, subgroup 4 and figure 3 herein.

4.3.3 Avalanche energy test. The avalanche energy test is to be performed in accordance with method 4064 of MIL-STD-750 using the circuit as shown on figure 4 or equivalent. The Schottky rectifier under test must be capable of absorbing the reverse energy, as follows: $I_{AS} = 1$ A, $V_{BR} = 100$ V minimum, $L = 100$ μH .

4.4 Conformance inspection. Conformance inspection shall be in accordance with MIL-PRF-19500.

4.4.1 Group A inspection. Group A inspection shall be conducted in accordance with appendix E, table E-V of MIL-PRF-19500, and table I herein. Electrical measurements (end-points) and delta requirements shall be in accordance with the applicable steps of table II herein.

4.4.2 Group B inspection. Group B inspection shall be conducted in accordance with the conditions specified for subgroup testing in tables E-VIa (JANS) and E-VIb (JAN, JANTX, and JANTXV) of MIL-PRF-19500 and as follows. Electrical measurements (end-points) shall be in accordance with table I, subgroup 2, forward voltage test (V_{F1}) and reverse leakage test (I_{R1}) herein. Delta measurements shall be in accordance with table II herein.

4.4.2.1 Group B inspection, table E-VIa (JANS) of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
B4	1037	$\Delta T_C = +85^\circ\text{C}$, $I_F = 2$ A minimum for 2,000 cycles.
B5	1038	Condition A, $V_R = 80$ V dc, $T_J = +125^\circ\text{C}$, $t = 340$ hours min; heat sinking allowed. This test shall be extended to 1,000 on each JANS wafer lot.

4.4.2.2 Group B inspection, table E-VIb (JAN, JANTX, and JANTXV) of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
B3	1037	$\Delta T_C = +85^\circ\text{C}$, $I_F = 2$ A minimum for 2,000 cycles.

4.4.3 Group C inspection. Group C inspection shall be conducted in accordance with the conditions specified for subgroup testing in table E-VII of MIL-PRF-19500. Electrical measurements (end-points) shall be in accordance with table I, subgroup 2, forward voltage test (V_{F1}) and reverse leakage test (I_{R1}) herein. Delta measurements shall be in accordance with table II herein.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
C2	2036	Condition A, weight = 10 lbs, $t = 15$ seconds
C5	4081	Limit for thermal resistance for 1N7070CCT3 is 2.0°C/W for each diode.
C6	1037	$\Delta T_C = +85^\circ\text{C}$, $I_F = 2$ A minimum for 6,000 cycles.
C6	1038	Condition A, $V_R = 80$ V dc, $T_J = +125^\circ\text{C}$, $t = 1,000$ hours minimum (for TX, TXV only); (heat sinking allowed).

4.4.4 Group E inspection. Group E inspection shall be conducted in accordance with the tests and conditions specified for subgroup testing in table E-IX of MIL-PRF-19500, and table III herein. Delta measurements shall be in accordance with table II herein.

4.5 Methods of inspection. Methods of inspection shall be as specified in the appropriate tables as follows.

4.5.1 Pulse measurements. Conditions for pulse measurement shall be as specified in section 4 of MIL-STD-750.

TABLE I. Group A inspection.

Inspection 1/	MIL-STD-750		Symbol	Limits		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 1</u>						
Visual and mechanical examination	2071					
<u>Subgroup 2</u>						
Thermal impedance	3101		Z _{θJX}			°C/W
Forward voltage 1N7070CCT3	4011	Pulsed test (see 4.5.1) I _F = 8 A (pk)	V _{F1}		.75	V dc
Forward voltage 1N7070CCT3	4011	Pulsed test (see 4.5.1) I _F = 16 A (pk)	V _{F2}		.95	V dc
Reverse current 1N7070CCT3	4016	DC method V _R = 100 V	I _{R1}		10	μA dc
<u>Subgroup 3</u>						
High temperature operation:		T _C = +125 °C				
Forward voltage 1N7070CCT3	4011	Pulsed test (see 4.5.1) I _F = 8 A (pk)	V _{F3}		.66	V dc
Forward voltage 1N7070CCT3	4011	Pulsed test (see 4.5.1) I _F = 16 A (pk)	V _{F4}		.85	V dc
Reverse current 1N7070CCT3	4016	DC method; V _R = 100 V	I _{R2}		10.0	mA dc
Low temperature operation:		T _C = -55°C				
Forward voltage 1N7070CCT3	4011	Pulsed test (see 4.5.1) I _F = 8 A (pk)	V _{F5}		.77	V dc
Forward voltage 1N7070CCT3	4011	Pulsed test (see 4.5.1) I _F = 16 A (pk)	V _{F6}		.98	V dc

See footnotes at end of table.

TABLE I. Group A inspection - Continued.

Inspection <u>1/</u> <u>2/</u>	MIL-STD-750		Symbol	Limits		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 4</u>						
Junction capacitance 1N7070CCT3	4001	$V_R = 5 \text{ V dc}$, $f = 1 \text{ MHz}$, $V_{SIG} = 50 \text{ mV (p-p)}$	C_J		430	pF
<u>Subgroup 5</u>						
Not applicable						
<u>Subgroup 6</u>						
Surge 1N7070CCT3	4066	See 1.3, column 4 herein, ten surges each diode. 60 seconds between surges, (see 4.5.1)				
Electrical measurements		See table I, subgroup 2 herein				
<u>Subgroup 7</u>						
Dielectric withstanding voltage	1016	$V_R = 500 \text{ V dc}$; all leads shorted; measure from leads to case	DWV		10	μA
Scope display evaluation	4023	Stable only.				
Electrical measurements		See table I, subgroup 2 herein				

1/ For sampling plan, see MIL-PRF-19500.

TABLE II. Groups B, C, and E delta requirements. 1/ 2/ 3/ 4/ 5/ 6/

Step	Inspection	MIL-STD-750		Symbol	Limits		Unit
		Method	Conditions		Min	Max	
1.	Forward voltage 1N7070CCT3	4011	pulsed (see 4.5.1) $I_F = 8 \text{ A (pk)}$	ΔV_{F1}	$\pm 50 \text{ mV dc}$ from initial reading.		
	Forward voltage 1N7070CCT3		4011				
2.	Reverse current 1N7070CCT3	4016	$V_R = 100\text{V}$	ΔI_{R1}	± 100 percent from initial reading or $\pm 2 \text{ uA}$ whichever is greater.		
3.	Thermal impedance	3101	See 4.3.2	$Z_{\Theta JX}$			

1/ Each individual diode.

2/ The electrical measurements for table E-VIa (JANS) of MIL-PRF-19500 are as follows:

- a. Subgroup 4, see table II herein, steps 1, 2, and 3.
- b. Subgroup 5, see table II herein, steps 1 and 2.

3/ The electrical measurements for table E-VIb (JANTX and JANTXV) of MIL-PRF-19500 are as follows:

- a. Subgroup 2, see table II herein, steps 1, 2, and 3.
- b. Subgroup 3, see table II herein, steps 1, 2, and 3.
- c. Subgroup 6, see table II herein, steps 1 and 2.

4/ The electrical measurements for table E-VII of MIL-PRF-19500 are as follows:

- a. Subgroups 2 and 3, see table II herein, steps 1, 2, and 3 for all levels.
- b. Subgroup 6, see table II herein, steps 1, 2, and 3 for all levels.

5/ Devices which exceed the table I limits for this test shall not be accepted.

6/ The electrical measurements for table E-IX of MIL-PRF-19500 are as follows:

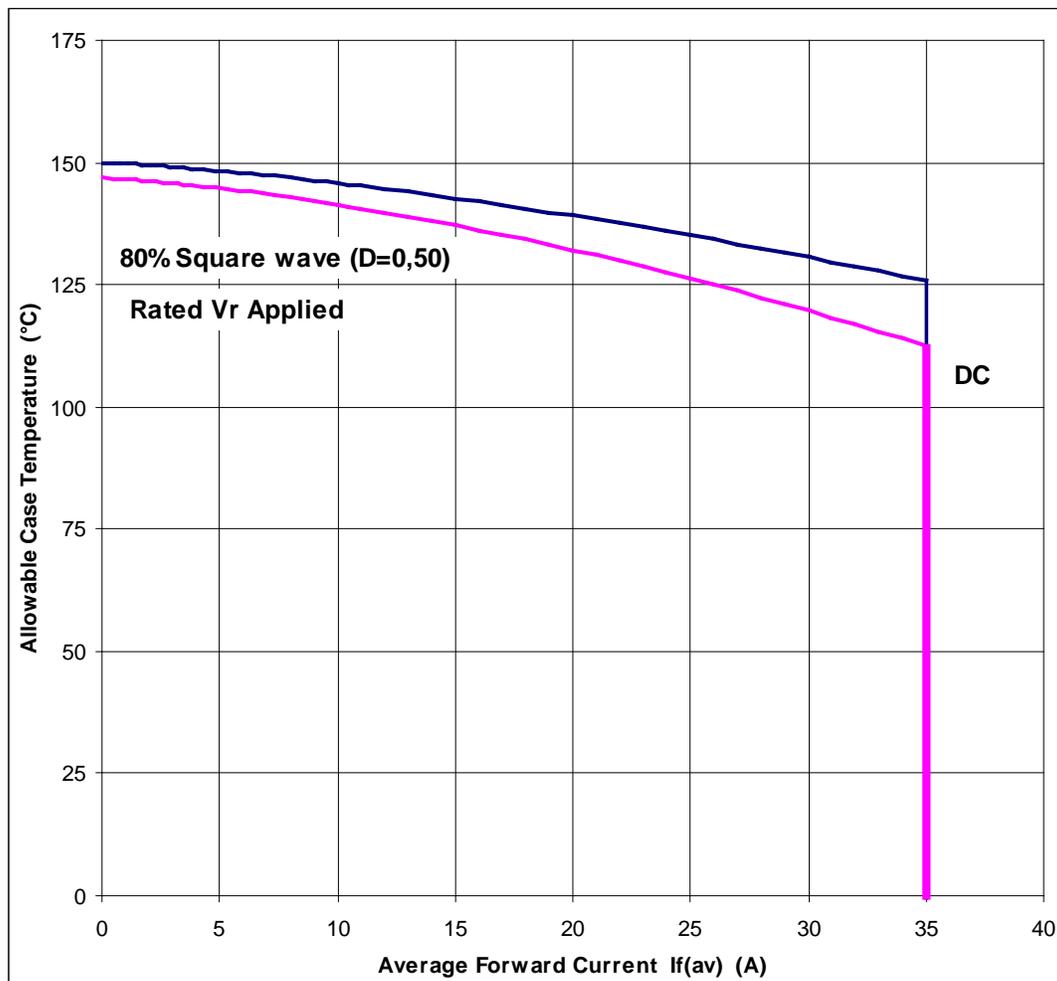
- a. Subgroup 1, see table III herein, steps 1, 2, and 3.
- b. Subgroup 2, see table III herein, steps 1 and 2.

TABLE III. Group E inspection (all quality levels) – for qualification and requalification only.

Inspection	MIL-STD-750		Qualification
	Method	Conditions	
<u>Subgroup 1</u>			n = 12, c = 0
Temperature cycling (air to air)	1051	Test condition G, 500 cycles, -55°C to +150°C.	
Hermetic seal	1071		
Electrical measurements		See table I, subgroup 2 and table II herein.	
<u>Subgroup 2</u>			n = 12, c = 0
Life test	1048	t = 1,000 hours, T _J = +125°C, V _R = 80 percent rated voltage (see 1.3, column 2 herein).	
Electrical measurements		See table I subgroup 2 and table II herein.	
<u>Subgroup 4</u>			
Thermal impedance curves		See MIL-PRF-19500.	
<u>Subgroup 6</u>			n = 3
ESD	1020		
<u>Subgroup 10</u> ^{1/}			n = 5, c = 0
Surge 1N7070CCT3	4066	Condition A, T _A = +25°C, I _{FSM} = 250 A, ten surges of 8.3 ms superimposed on I _O . V _R = 0; I _O = 10 A pk half sine wave, continuous.	
Electrical measurements		See table I subgroup 2 (V _F and I _R only).	

^{1/} Each individual diode.

TEMPERATURE-CURRENT DERATING CURVE 1N7070CCT3



SWITCH MODE OPERATION 80% D/C T_C (°C) (CASE)
 $R_{\theta JC} = 1.0$ °C/W

NOTES:

1. All devices are capable of operating at $\leq T_J$ specified on this curve. Any parallel line to this curve will intersect the appropriate current for the desired maximum T_J allowed.
2. Derate design curve constrained by the maximum junction temperature ($T_J \leq 150^\circ\text{C}$) and current rating specified. (See 1.3 herein.)
3. Derate design curve chosen at $T_J \leq 125^\circ\text{C}$, where the maximum temperature of electrical test is performed.
4. Derate design curves chosen at $T_J \leq 125^\circ\text{C}$, and 110°C to show current rating where most users want to limit T_J in their application.

FIGURE 2. Temperature-current derating curve (entire package) for 1N7070CCT3.

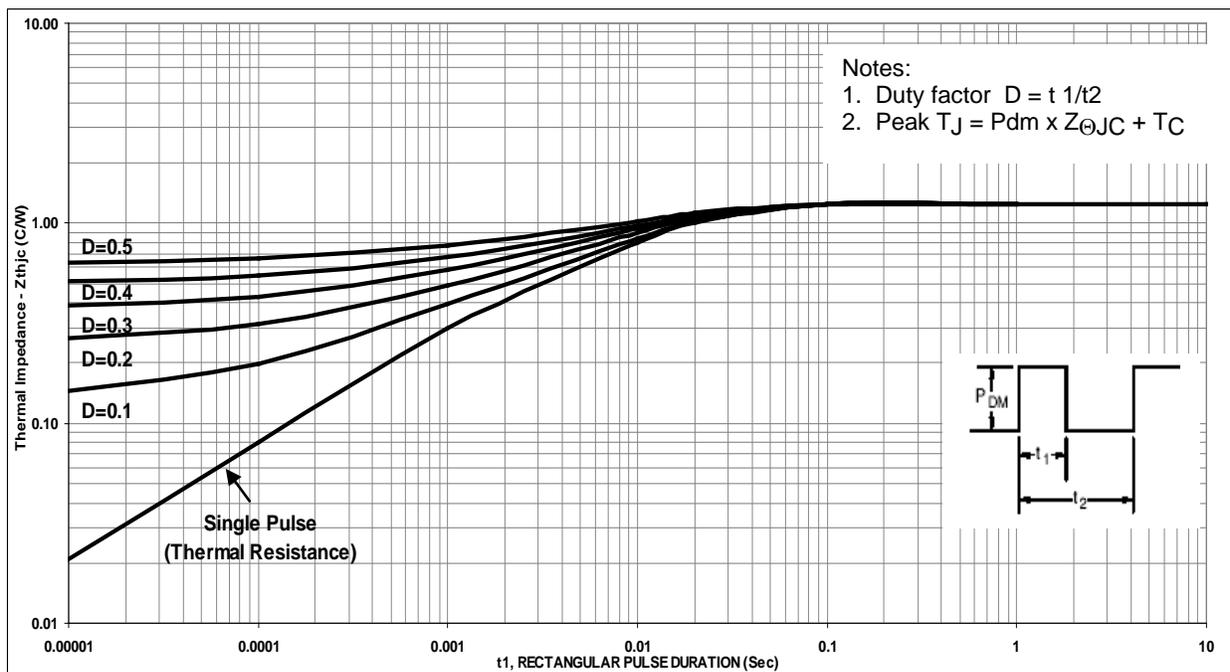
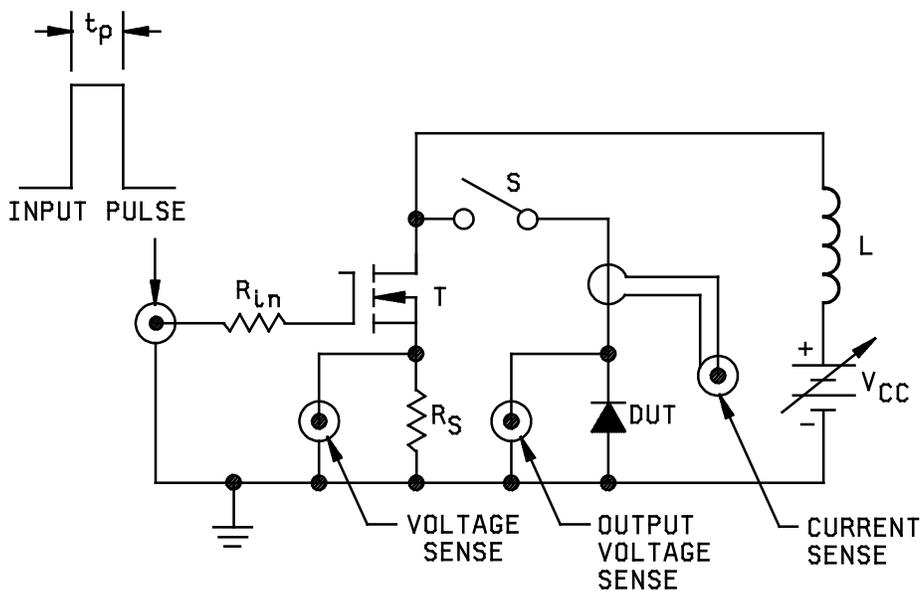


FIGURE 3. Thermal impedance (for each leg). 1N7070CCT3.



Input pulse $R_{in} = 50$ ohms, 1 watt
 $V_G = 10$ Volts, $R_S = 0.1$ ohms, 1 watt
 $Z_G = 50$ ohms
 $L = 150$ mH
 $P.W. \approx 30$ μ s
 Duty cycle ≤ 1 percent, T = IRF350/2N6768 or equivalent

Procedure:

1. With S open, adjust pulse width to test current of 1 amp across R_S .
2. Close S, verify test current with current sense.
3. Read peak output voltage (see 4.3.3).

FIGURE 4. Peak reverse energy test circuit.

5. PACKAGING

5.1 Packaging. For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When packaging of materiel is to be performed by DoD or in-house contractor personnel, these personnel need to contact the responsible packaging activity to ascertain packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activities within the Military Service or Defense Agency, or within the Military Service's system commands. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

6. NOTES

(This section contains information of a general or explanatory nature that may be helpful, but is not mandatory. The notes specified in MIL-PRF-19500 are applicable to this specification.)

6.1 Intended use. Semiconductors conforming to this specification are intended for original equipment design applications and logistic support of existing equipment.

6.2 Acquisition requirements. Acquisition documents should specify the following:

- a. Title, number, and date of this specification.
- b. Packaging requirements (see 5.1).
- c. Lead material, finish, and formation (see 3.4.2).
- d. Product assurance level and type designator.

6.3 Qualification. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers List (QML 19500) whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from Defense Supply Center, Columbus, ATTN: DSCC/VQE, P.O. Box 3990, Columbus, OH 43218-3990 or e-mail vqe.chief@dla.mil . An online listing of products qualified to this specification may be found in the Qualified Products Database (QPD) at <https://assist.daps.dla.mil> .

6.4 Cross reference substitution list. A PIN for PIN replacement table follows, and these devices are directly interchangeable.

Non-preferred PIN	Preferred PIN
16CYQ100C	JANS, JANTXV, JANTX, JAN1N7070CCT3

Custodians:
 Army - CR
 Navy - EC
 Air Force - 85
 NASA - NA
 DLA - CC

Preparing activity:
 DLA - CC
 (Project 5961-2009-056)

Review activity:
 Air Force - 99

NOTE: The activities listed above were interested in this document as of the date of this document. Since organizations and responsibilities can change, you should verify the currency of the information above using the ASSIST Online database at <https://assist.daps.dla.mil> .